HALL IC

S-5711A Series

The S-5711A Series, developed by CMOS technology, is a Hall IC with a high-sensitivity and operates on a low current.

The output voltage changes when the S-5711A Series detects the intensity level of flux density. Using the S-5711A Series with a magnet makes it possible to detect the open/close state in various devices.

High-density mounting is possible by using the super-small SNT-4A, SOT-23-3 packages. Also, the S-5711A Series is the most suitable for portable devices due to the low current consumption.

■ Features

· Built-in chopping stabilized amplifier

Applicable in various devices with wide range of option

: Detection of both poles, south pole or north pole*1

: Active "L", active "H" *1

: Nch open drain output, CMOS output

• Wide power supply voltage range: 2.4 V to 5.5 V

• Low current consumption : 5.0 μA typ., 8.0 μA max.

• Range of operation temperature: -40°C to +85°C

Small magnetic characteristics against temperature dependency

• Small package : SNT-4A, SOT23-3

• Lead-free product

*1. Selectable by option

Please contact our sales office for options other than those specified in "■ Product Name Structure", "2. Product name list".

■ Applications

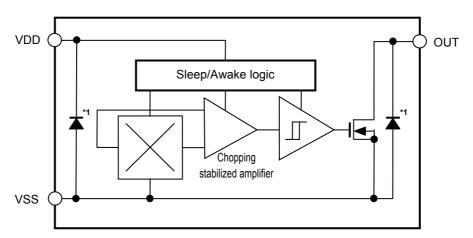
- Cellular phones (flip type, slide type, etc.)
- Laptop PCs
- Digital video cameras
- Playthings, portable games
- · Home appliances

■ Packages

Daakaga Nama		Drawing Code							
Package Name	Package	Tape	Reel	Land					
SNT-4A	PF004-A	PF004-A PF		PF004-A					
SOT-23-3	MP003-C MP003-C MP003-Z		MP003-Z	_					

■ Block Diagrams

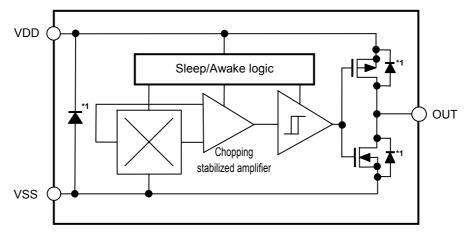
1. Nch open drain output product



*1. Parasitic diode

Figure 1

2. CMOS output product



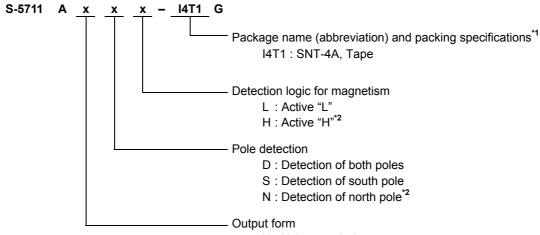
*1. Parasitic diode

Figure 2

■ Product Name Structure

1. Product name

(1) SNT-4A

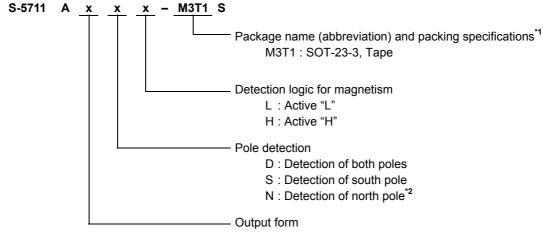


N : Nch open drain output

C: CMOS output

- *1. Refer to the tape specifications at the end of this book.
- *2. Selectable by option

(2) SOT-23-3



N: Nch open drain output

C : CMOS output

- *1. Refer to the tape specifications at the end of this book.
- *2. Selectable by option

2. Product name list

Table 1

Output Form	Pole Detection	Detection Logic for Magnetism	SNT-4A	SOT-23-3
Nch open drain output	Both poles	Active "L"	S-5711ANDL-I4T1G	S-5711ANDL-M3T1S
CMOS output	Both poles	Active "L"	S-5711ACDL-I4T1G	S-5711ACDL-M3T1S
CMOS output	Both poles	Active "H"	_	S-5711ACDH-M3T1S
Nch open drain output	South pole	Active "L"	S-5711ANSL-I4T1G	S-5711ANSL-M3T1S
CMOS output	South pole	Active "L"	S-5711ACSL-I4T1G	S-5711ACSL-M3T1S

Remark Please contact our sales office for options other than those specified above.

■ Pin Configurations

SNT-4A Top view

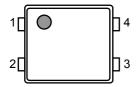


Figure 3

SOT-23-3 Top view

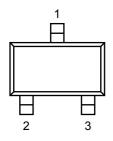


Figure 4

Table 2

Pin No.	Symbol	Pin Description
1	VDD	Power supply pin
2	VSS	GND pin
3	NC ^{*1}	No connection
4	OUT	Output pin

^{*1.} The NC pin is electrically open.

The NC pin can be connected to VDD or VSS.

Table 3

Pin No.	Symbol	Pin Description
1	VSS	GND pin
2	VDD	Power supply pin
3	OUT	Output pin

■ Absolute Maximum Ratings

Table 4

(Ta = 25°C unless otherwise specified)

			,	
	Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltag	je	V_{DD} V_{SS} -0.3 to V_{SS} +7.0		V
Output voltage	Nch open drain output		V_{SS} –0.3 to V_{SS} +7.0	V
Output voltage	CMOS output	V _{OUT}	V_{SS} –0.3 to V_{DD} +0.3	V
Dower dissination	SNT-4A	В	300 ^{*1}	mW
Power dissipation	SOT-23-3	- P _D	430 ^{*1}	mW
Operating ambient t	emperature	T _{opr}	T _{opr} —40 to +85	
Storage temperature	Storage temperature		-40 to +125	°C

^{*1.} When mounted on board

[Mounted board]

(1) Board size: 114.3 mm × 76.2 mm × t1.6 mm(2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

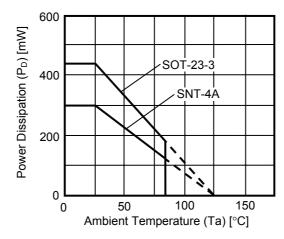


Figure 5 Power Dissipation of Package (When Mounted on Board)

■ Electrical Characteristics

1. Nch open drain output product

Table 5

(Ta = 25°C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Circuit
Power supply voltage	V_{DD}	_	2.4	3.0	5.5	V	-
Current consumption	I_{DD}	Average value	_	5.0	8.0	μΑ	1
Output current	I _{OUT}	Output transistor Nch, V _{OUT} = 0.4 V	1	ı	-	mA	2
Leakage current	I _{LEAK}	Output transistor Nch, V _{OUT} = 5.5 V	_	ı	1	μΑ	2
Awake mode time	t _{AW}	_	_	130	-	μs	-
Sleep mode time	t _{SL}	_	_	50	100	ms	_

2. CMOS output product

Table 6

(Ta = 25°C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

		(: a = 0 0; : DD	0.0 ., .	3		000	00000
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Circuit
Power supply voltage	V_{DD}	-	2.4	3.0	5.5	V	_
Current consumption	I _{DD}	Average value	-	5.0	8.0	μΑ	1
Output ourront		Output transistor Nch, V _{OUT} = 0.4 V	1	_	_	mA	2
Output current	IOUT	Output transistor Pch, V _{OUT} = V _{DD} -0.4 V	-	_	-1	mA	2
Awake mode time	t _{AW}	_	_	130	-	μs	_
Sleep mode time	t _{SL}	-	_	50	100	ms	_

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■ Magnetic Characteristics

1. Product with detection of both poles

Table 7

(Ta = 25°C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Circuit
Operating point*1	S pole	B _{OPS}	_	_	3.8	6.0	mT	3
Operating point	N pole	B _{OPN}	_	-6.0	-3.8	-	mT	3
Release point*2	S pole	B _{RPS}	_	0.5	2.8	-	mT	3
Release point	N pole	B _{RPN}	_	-	-2.8	-0.5	mT	3
Hysteresis width*3	S pole	B _{HYSS}	$B_{HYSS} = B_{OPS} - B_{RPS}$	-	1.0	1	mT	3
nysteresis width	N pole	B _{HYSN}	$B_{HYSN} = B_{OPN} - B_{RPN} $	_	1.0	-	mT	3

2. Product with detection of south pole

Table 8

(Ta = 25° C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Circuit
Operating point*1	S pole	B _{OPS}	-	-	3.8	6.0	mT	3
Release point*2	S pole	B _{RPS}	_	0.5	2.8	_	mT	3
Hysteresis width*3	S pole	B _{HYSS}	$B_{HYSS} = B_{OPS} - B_{RPS}$	_	1.0	_	mT	3

3. Product with detection of north pole*4

Table 9

(Ta = 25° C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Circuit
Operating point*1	N pole	B _{OPN}	_	-6.0	-3.8	ı	mT	3
Release point*2	N pole	B _{RPN}	_	_	-2.8	-0.5	mT	3
Hysteresis width*3	N pole	B _{HYSN}	$B_{HYSN} = B_{OPN} - B_{RPN} $	1	1.0	1	mT	3

***1.** B_{OPN}, B_{OPS}: Operating points

The operating points are the values of magnetic flux density when the output voltage (V_{OUT}) is inverted after the magnetic flux density applied to the S-5711A Series by the magnet (N or S pole) is increased (the magnet is moved closer). Even when the magnetic flux density exceeds B_{OPN} or B_{OPS} , V_{OUT} retains the status.

*2. B_{RPN}, B_{RPS}: Release points

The release points are the values of magnetic flux density when the output voltage (V_{OUT}) is inverted after the magnetic flux density applied to the S-5711A Series by the magnet (N or S pole) is decreased (the magnet is moved further away). Even when the magnetic flux density falls below B_{RPN} or B_{RPS} , V_{OUT} retains the status.

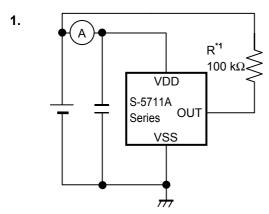
***3.** B_{HYSN}, B_{HYSS} : Hysteresis widths

B_{HYSN} and B_{HYSS} are the difference between B_{OPN} and B_{RPN}, and B_{OPS} and B_{RPS}, respectively.

*4. Selectable by option

Remark The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

■ Test Circuits



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 6

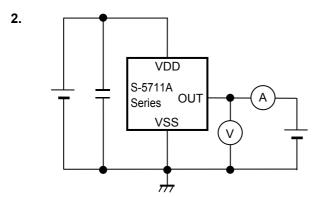
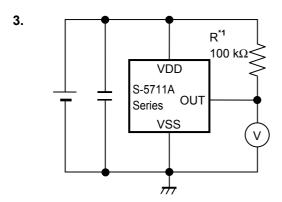


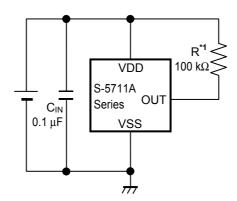
Figure 7



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 8

■ Standard Circuit



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 9

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

1. Direction of applied magnetic flux and position of Hall sensor

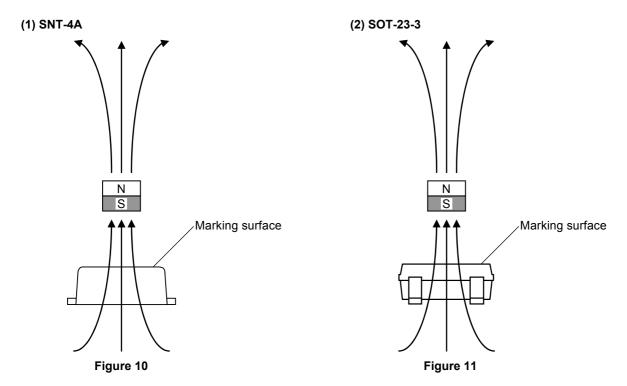
The S-5711A Series detects the flux density which is vertical to the marking surface.

In products with detection of both poles, the output voltage (V_{OUT}) is inverted when the south or north pole is moved closer to the marking surface.

In products with detection of the south pole, the output voltage (V_{OUT}) is inverted when the south pole is moved closer to the marking surface.

In products with detection of the north pole, the output voltage (V_{OUT}) is inverted when the north pole is moved closer to the marking surface.

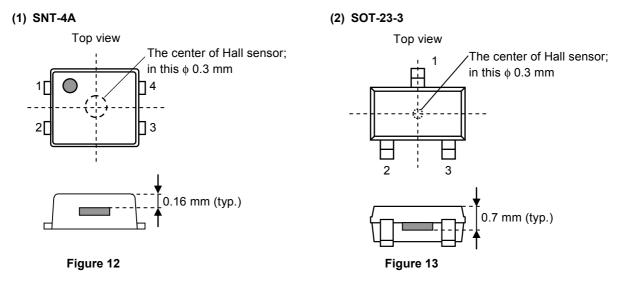
Figures 10 and 11 show the direction in which magnetic flux is being applied.



Figures 12 and 13 show the position of Hall sensor.

The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.

The following also shows the distance (typ. value) between the marking surface and the chip surface of a package.



2. Basic operation

The S-5711A Series changes the output voltage level (V_{OUT}) according to the level of the magnetic flux density (north or south pole) applied by a magnet.

The following explains the operation when the magnetism detection logic is active "L".

(1) Products with detection of both poles

When the magnetic flux density vertical to the marking surface exceeds B_{OPN} or B_{OPS} after the south or north pole of a magnet is moved closer to the marking surface of the S-5711A Series, V_{OUT} changes from "H" to "L". When the south or north pole of a magnet is moved further away from the marking surface of the S-5711A Series and the magnetic flux density is lower than B_{RPN} or B_{RPS} , V_{OUT} changes from "L" to "H".

(2) Products with detection of south pole

When the magnetic flux density vertical to the marking surface exceeds B_{OPS} after the south pole of a magnet is moved closer to the marking surface of the S-5711A Series, V_{OUT} changes from "H" to "L". When the south pole of a magnet is moved further away from the marking surface of the S-5711A Series and the magnetic flux density is lower than B_{RPS} , V_{OUT} changes from "L" to "H".

(3) Products with detection of north pole*1

When the magnetic flux density vertical to the marking surface exceeds B_{OPN} after the north pole of a magnet is moved closer to the marking surface of the S-5711A Series, V_{OUT} changes from "H" to "L". When the north pole of a magnet is moved further away from the marking surface of the S-5711A Series and the magnetic flux density is lower than B_{RPN} , V_{OUT} changes from "L" to "H".

*1. Selectable by option

Figures 14 to 16 show the relationship between the magnetic flux density and V_{OUT} .

(1) Products with detection of both poles

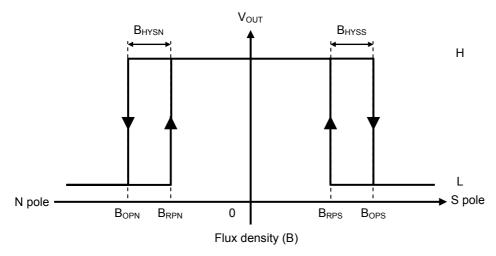


Figure 14

(2) Products with detection of south pole

(3) Products with detection of north pole

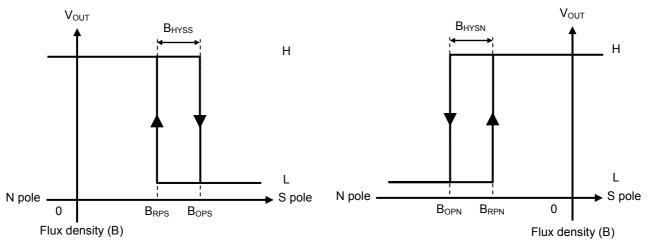


Figure 15 Figure 16

3. Time dependency in the current consumption

The S-5711A Series performs the intermittent operation. The S-5711A Series operates with low current consumption due to repeating the sleep mode (50 ms typ.) and the awake mode (130 μ s typ.).

Figure 17 shows the time dependency in the current consumption.

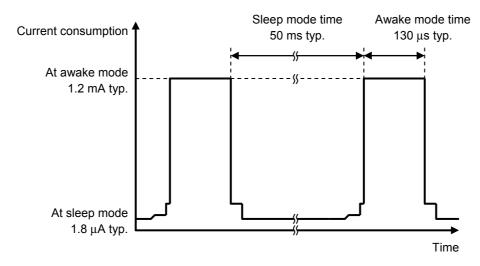


Figure 17

4. Timing chart

Figure 18 shows the operation timing of the S-5711A Series.

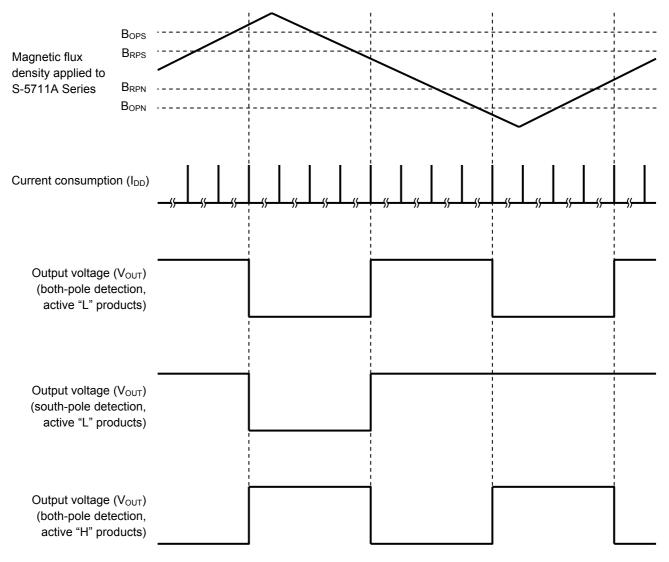


Figure 18

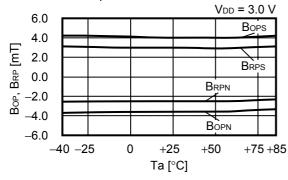
■ Precautions

- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by throughtype current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Large stress on this IC may affect on the magnetic characteristics. Avoid large stress which is caused by bend and distortion during mounting the IC on a board or handle after mounting.
- When designing for mass production using an application circuit described herein, the product deviation and temperature characteristics of the external parts should be taken into consideration. SII shall not bear any responsibility for patent infringements related to products using the circuits described herein.
- SII claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Characteristics (Typical Data)

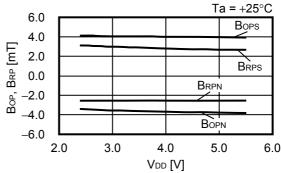
1. Operating point, release point (B_{OP}, B_{RP}) — Temperature (Ta)

Detection of both poles

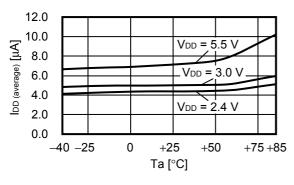


2. Operating point, release point (B_{OP} , B_{RP}) — Power supply voltage (V_{DD})

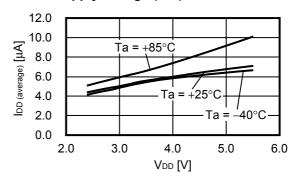
Detection of both poles



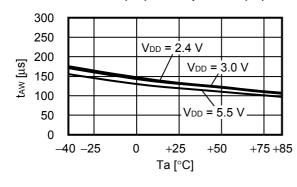
3. Current consumption (average) (I_{DD (average)}) – Temperature (Ta)



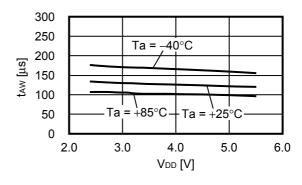
4. Current consumption (average) ($I_{DD (average)}$) — Power supply voltage (V_{DD})



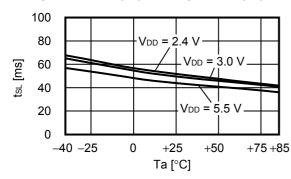
5. Awake mode time (t_{AW}) — Temperature (Ta)



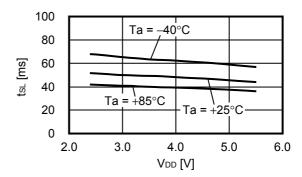
6. Awake mode time (t_{AW}) — Power supply voltage (V_{DD})



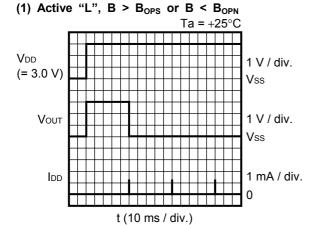
7. Sleep mode time (t_{SL}) — Temperature (Ta)

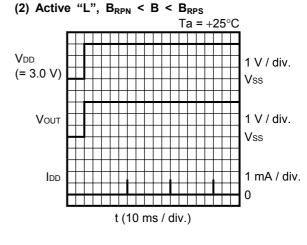


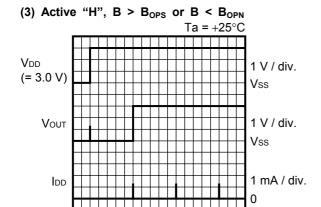
8. Sleep mode time (t_{SL}) — Power supply voltage (V_{DD})



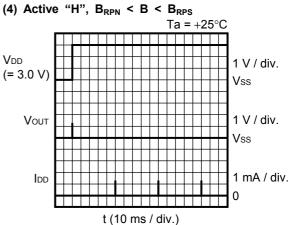
9. Start up response (Detection of both poles)







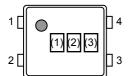
t (10 ms / div.)



■ Marking Specifications

(1) SNT-4A

SNT-4A Top view



(1) to (3): Product code (Refer to Product name vs. Product code.)

Product name vs. Product code

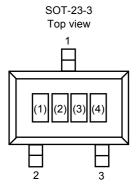
(a) Nch open drain output product

(1)						
Product Name	Product Code					
Floduct Name	(1)	(2)	(3)			
S-5711ANDL-I4T1G	T	Z	Α			
S-5711ANSL-I4T1G	Т	Z	Е			

(b) CMOS output product

Product Name	Product Code				
Floduct Name	(1)	(2)	(3)		
S-5711ACDL-I4T1G	Т	Z	1		
S-5711ACSL-I4T1G	Т	Z	5		

(2) SOT-23-3



- (1) to (3): Product code (Refer to Product name vs. Product code.)
- (4): Lot number

Product name vs. Product code

(a) Nch open drain output product

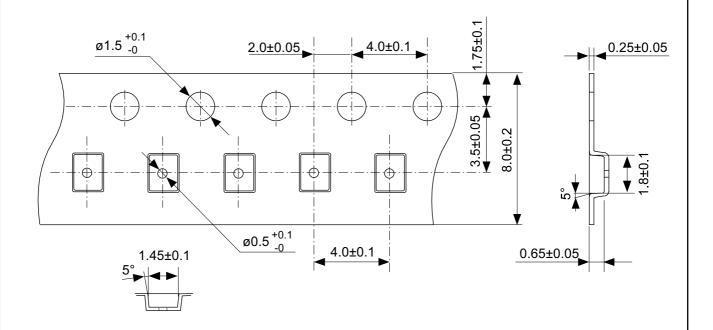
(-)			
Product Name	Product Code		
Floudet Name	(1)	(2)	(3)
S-5711ANDL-M3T1S	Т	Z	Α
S-5711ANSL-M3T1S	Т	Z	E

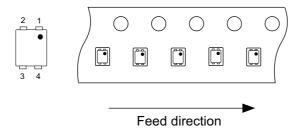
(b) CMOS output product

(a) since carpar product			
Product Name	Product Code		
Floduct Name	(1)	(2)	(3)
S-5711ACDL-M3T1S	Т	Z	1
S-5711ACDH-M3T1S	Т	Z	2
S-5711ACSL-M3T1S	Т	Z	5

TITLE	SNT-4A-A-PKG Dimensions	
No.	PF004-A-P-SD-4.0	
SCALE		
UNIT	mm	
Soiko Instrumento Inc		

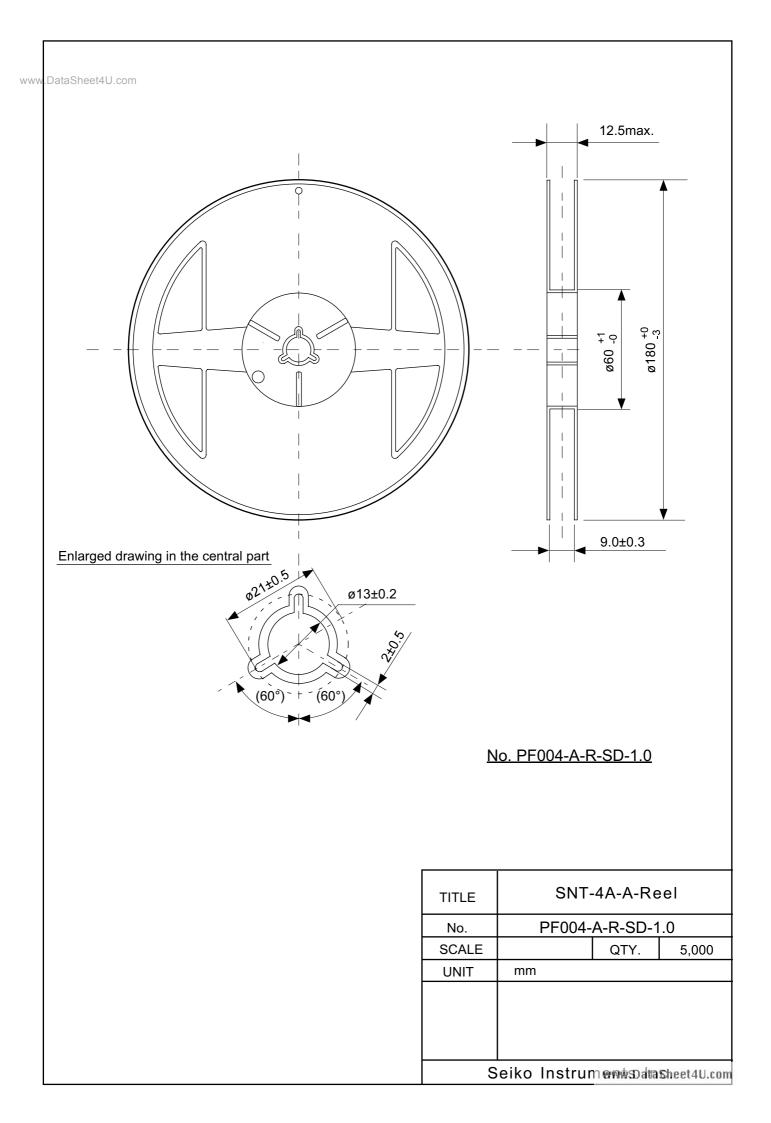
Seiko Instruments na Sheet4U.com



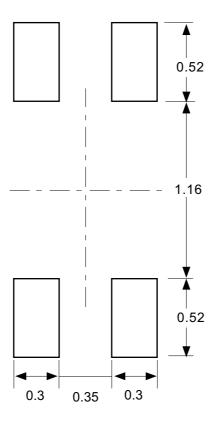


No. PF004-A-C-SD-1.0

TITLE	SNT-4A-A-Carrier Tape	
No.	PF004-A-C-SD-1.0	
SCALE		
UNIT	mm	
Seiko Instrum พพพ-DataSheet4U.com		



www.DataSheet4U.com

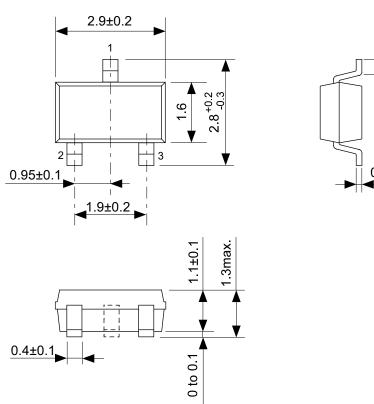


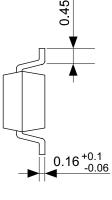
Caution Making the wire pattern under the package is possible. However, note that the package may be upraised due to the thickness made by the silk screen printing and of a solder resist on the pattern because this package does not have the standoff.

パッケージ下への配線パターン形成は可能ですが、本パッケージはスタンドオフが無いので、パターン上のレジスト厚み、シルク印刷の厚みによってパッケージが持ち上がることがありますのでご配慮ください。 注意

No. PF004-A-L-SD-3.0

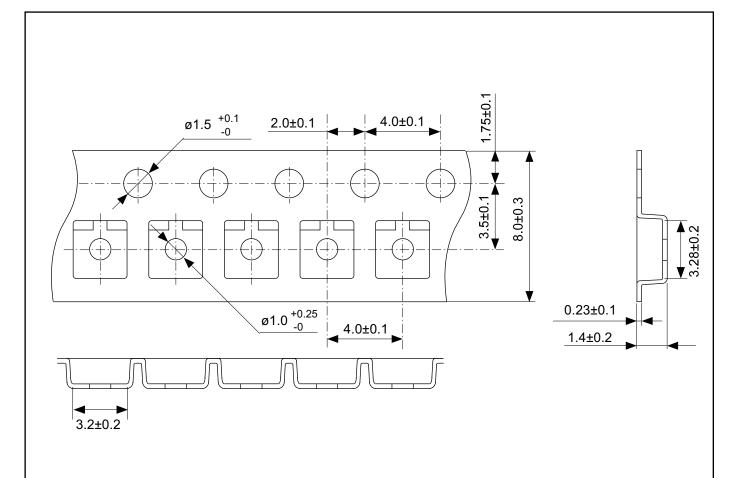
TITLE	SNT-4A-A-Land Recommendation	
No.	PF004-A-L-SD-3.0	
SCALE		
UNIT	mm	
Seiko Instrum ewwwsDataSheet4U.com		

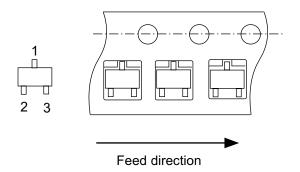




No. MP003-C-P-SD-1.0

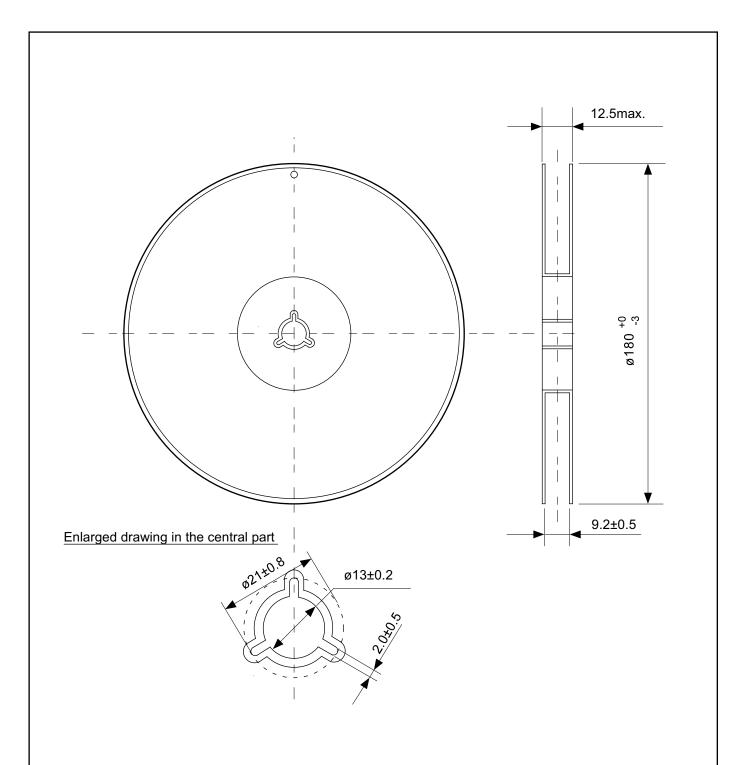
TITLE	SOT233-C-PKG Dimensions	
No.	MP003-C-P-SD-1.0	
SCALE		
UNIT	mm	
Seiko Instruments Inc.		





No. MP003-C-C-SD-1.0

TITLE	SOT233-C-Carrier Tape	
No.	MP003-C-C-SD-1.0	
SCALE		
UNIT	mm	
Seiko Instruments Inc.		



No. MP003-Z-R-SD-1.0

TITLE	SOT233-C-Reel		
No.	MP003-Z-R-SD-1.0		
SCALE		QTY.	3,000
UNIT	mm		
Seiko Instruments Inc.			

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